

<b>FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT</b>			<b>ATTY DOCKET NO.</b> 536-009.028		<b>SERIAL NO.</b> To be assigned <b>10/581127</b>	
<b>APPLICANT: B. HEINEMANN et al.</b>						
<b>FILING DATE:</b> Herewith			<b>ART UNIT:</b> To be assigned <b>D. Nhu</b>			
<b>UNITED STATES PATENT DOCUMENTS</b>						
EXAM. INITIAL	DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/DN/	2005/0023642	Feb. 03, 2005	Heinemann et al.			
	2003/0146477	Aug. 07, 2003	Krutsick			
	2003/0146468	Aug. 07, 2003	Gris et al.			
	2002/0168829	Nov. 14, 2002	Bock et al.			
/DN/	2003/0162360	Aug. 28, 2003	Beasom			
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO
/DN/	EP 0 746 038	Dec. 19, 2001	EP			
/DN/	2000188296	July 04, 2000	JP			
/DN/	2000269350	Sept. 29, 2000	JP			
<b>OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)</b>						
/DN/	1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.				
	2	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.				
	3	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.				
	4	D. V. Singh et al., "Novel epitaxial p-Si/n-Si <sub>1-x</sub> C <sub>x</sub> /p-Si heterojunction bipolar transistors," IEEE, 2000.				
	5	B. El-Kareh et al., "A 5V complementary -SiGe BiCMOS technology for high-speed precision analog circuits." Date unknown				
/DN/	6	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/n-Si <sub>1-x</sub> C <sub>x</sub> /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.				
Examiner (To be assigned) /David Nhu/			Date: 09/02/2010			

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EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	FILING DATE IF APPROPRIATE	
/DN/		2003/0219952	Nov. 27, 2003	Fujimaki			
/DN/		6,222,250	April 24, 2001	Gomi			
/DN/		4,719,185	Jan. 12, 1988	Goth			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	TRANSLATION YES/NO	
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	8	D. L. Harame et al., "55 GHz polysilicon-emitter graded SiGe-base PNP transistors," 1991, p. 71.					
	9	T. Onai et al., "Self-aligned complementary bipolar technology for low-power dissipation and ultra-high-speed LSIs," IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pp. 413-418.					
	10	S. J. Jeng et al., "A 210-GHz fr SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001.					
	11	J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.					
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